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PATENT ABSTRACTS OF JAPAN

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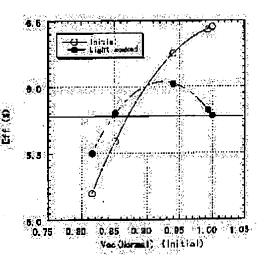
FUJIKAKE SHINJI

(54) NON-MONOCRYSTAL SOLAR BATTERY

(57)Abstract:

PROBLEM TO BE SOLVED: To improve efficiency after irradiation of light in a pin solar battery, using a nonmonocrystal thin film.

SOLUTION: The film thickness of a p-type semiconductor is set, so that an open voltage before irradiation of light can be set to 0.85-0.99 times as large as the maximum value of the open voltage before irradiation of light. The acceptor impurity concentration of the p-type semiconductor can be set so that the open voltage before the irradiation of light can be set so as to be 0.85-0.99 times as large as the maximum value of the open voltage before the irradiation of light. For the condition of irradiation of light, 10 hours or more is set for 1 SUN, or that (light intensity [SUN])2×(time [h]) is set at 10 or more.



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